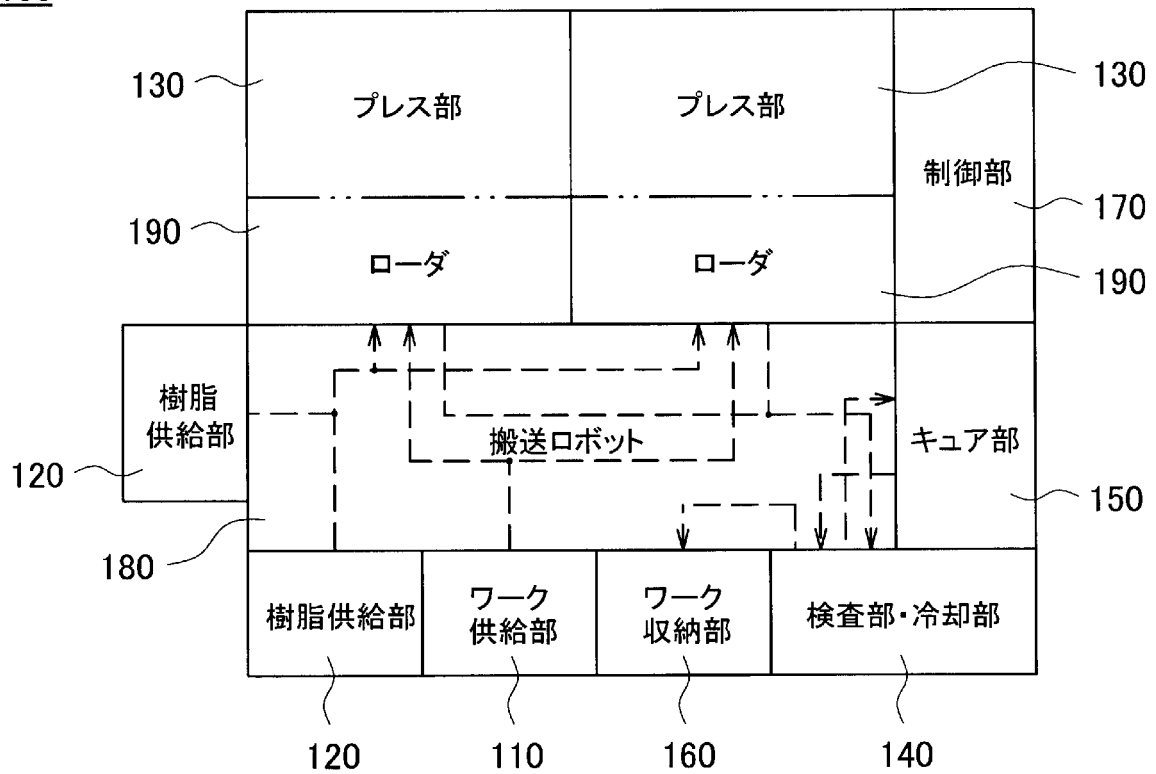


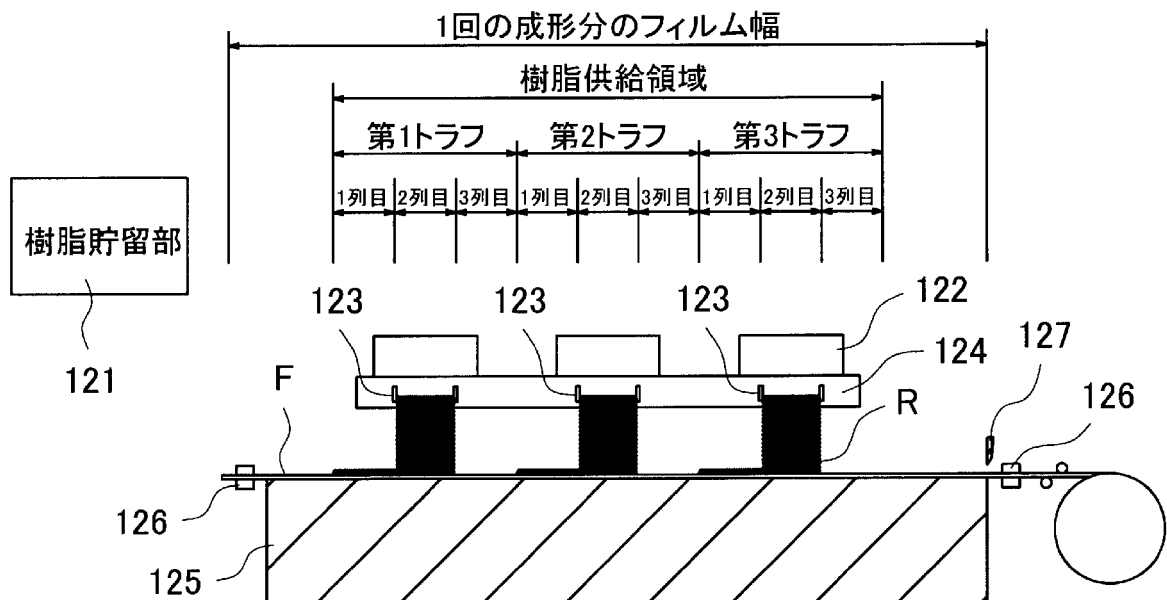
[図1]

100

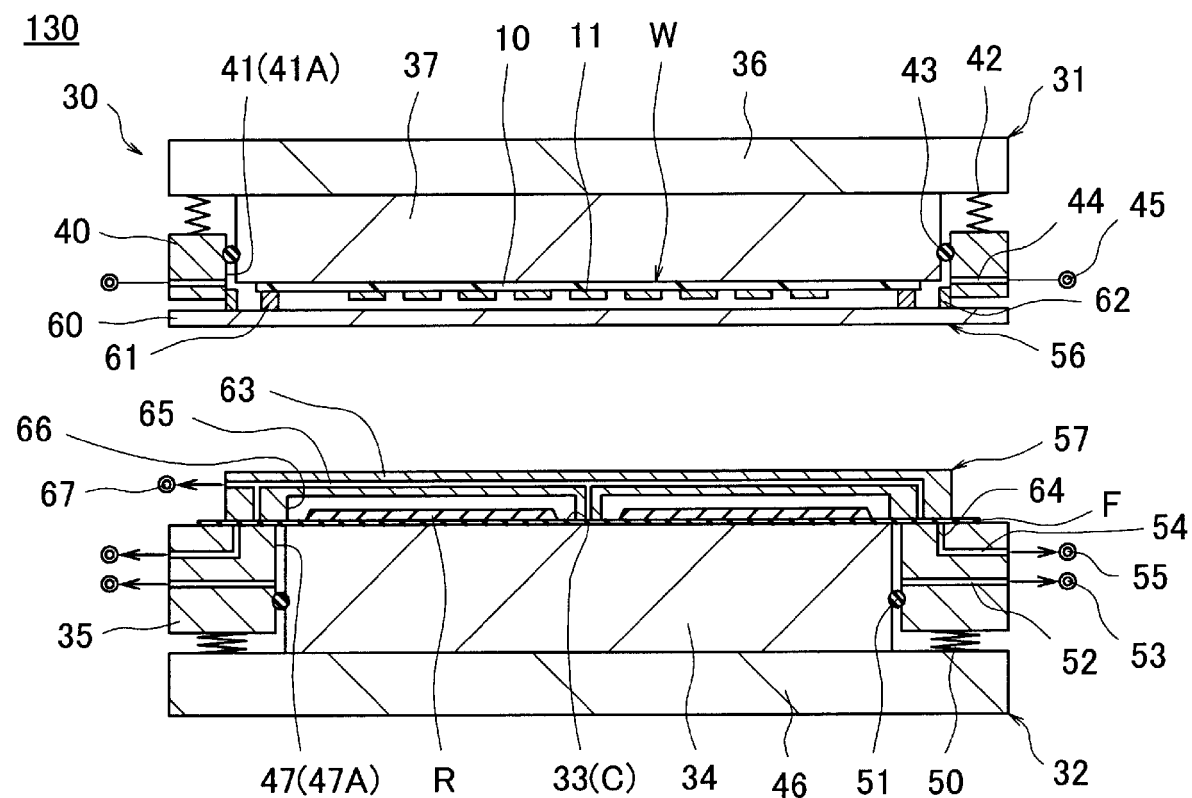


[図2]

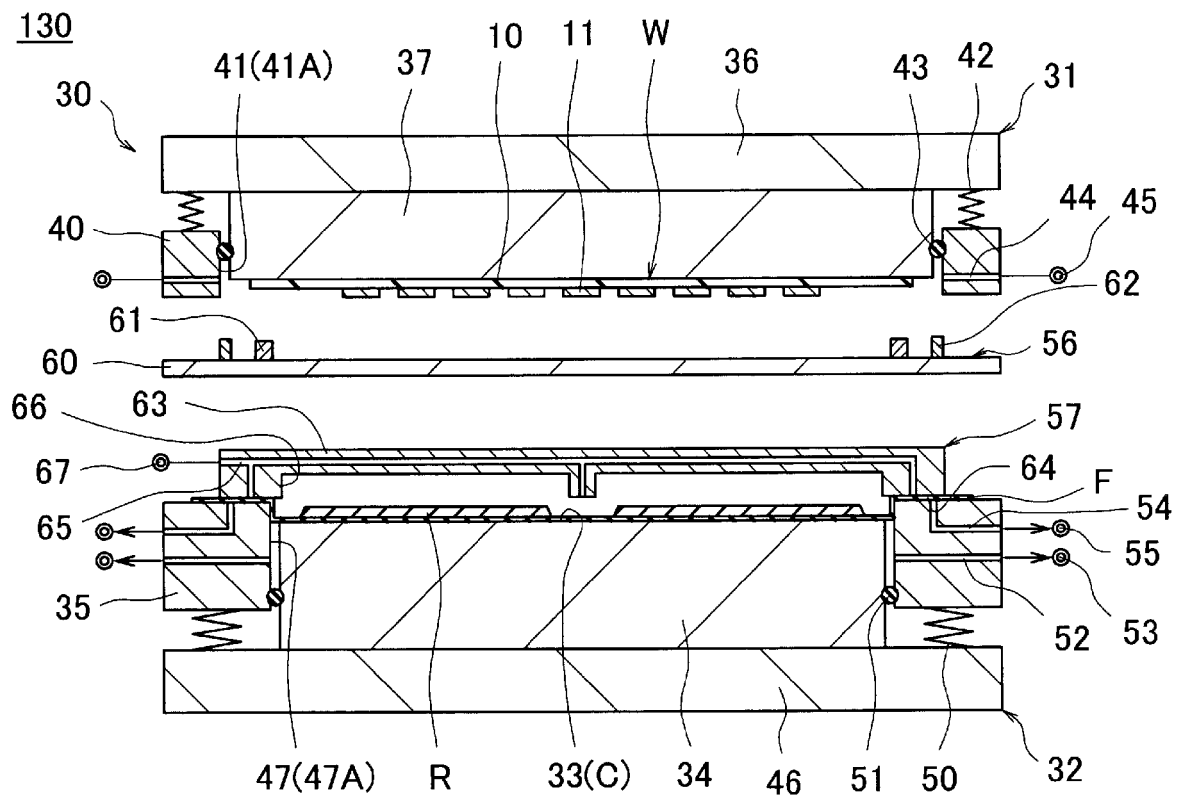
120



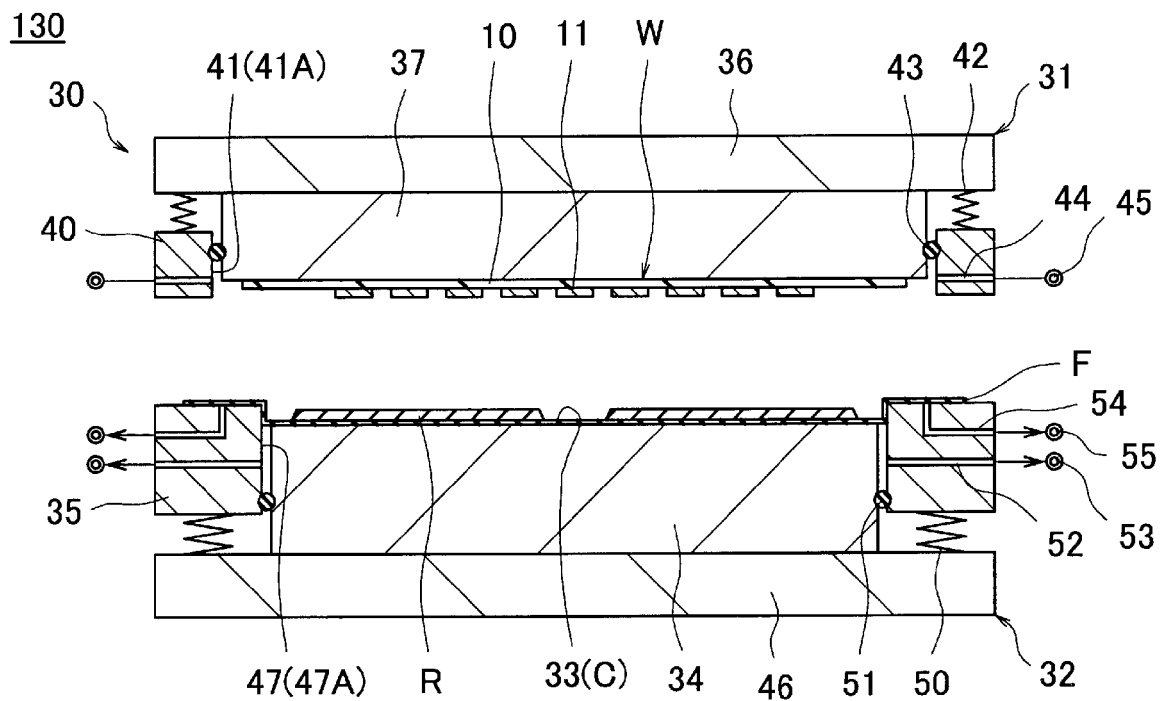
130



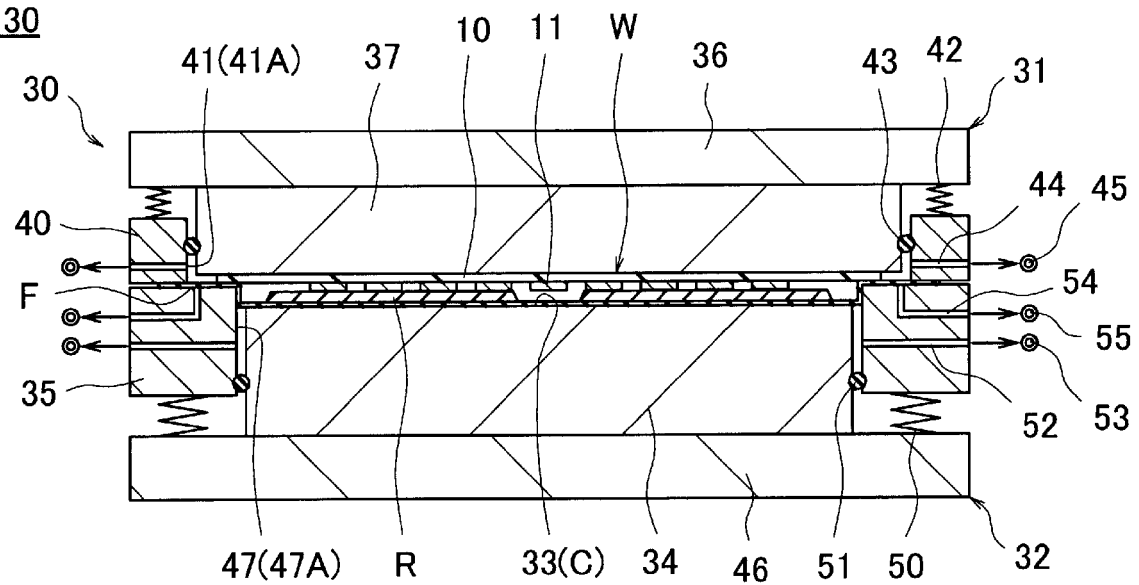
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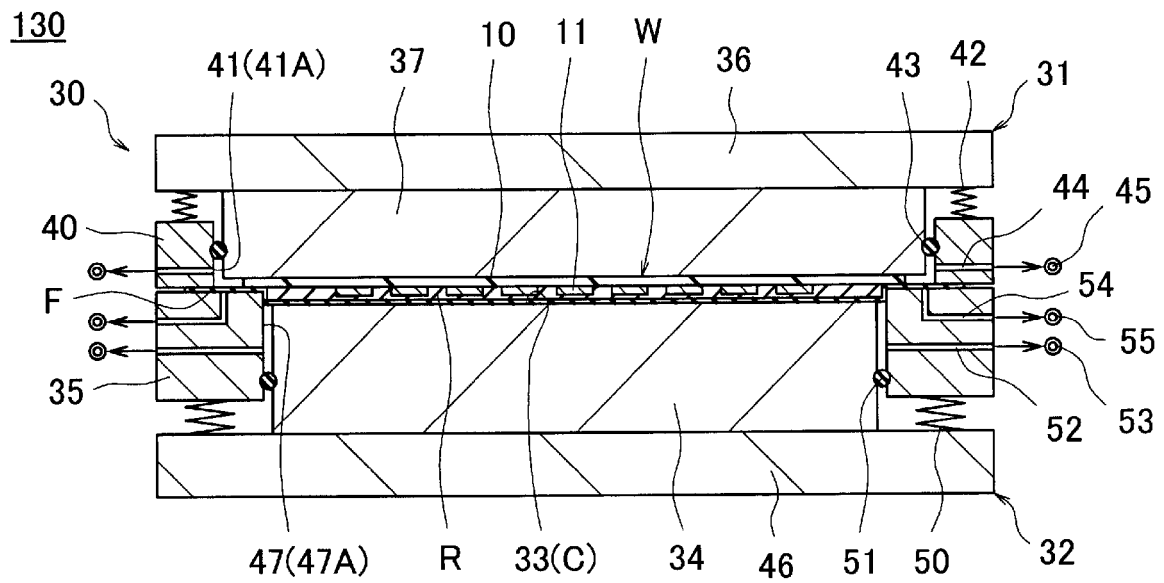
[図6]



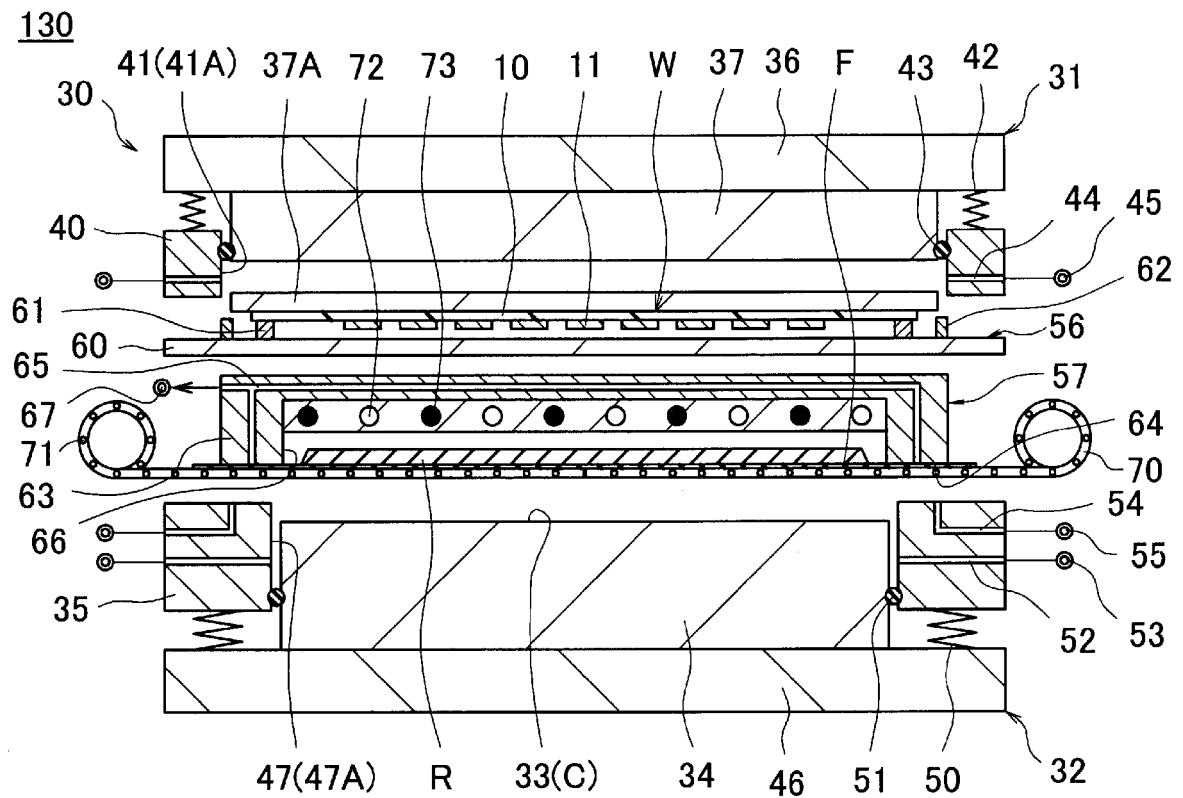
130



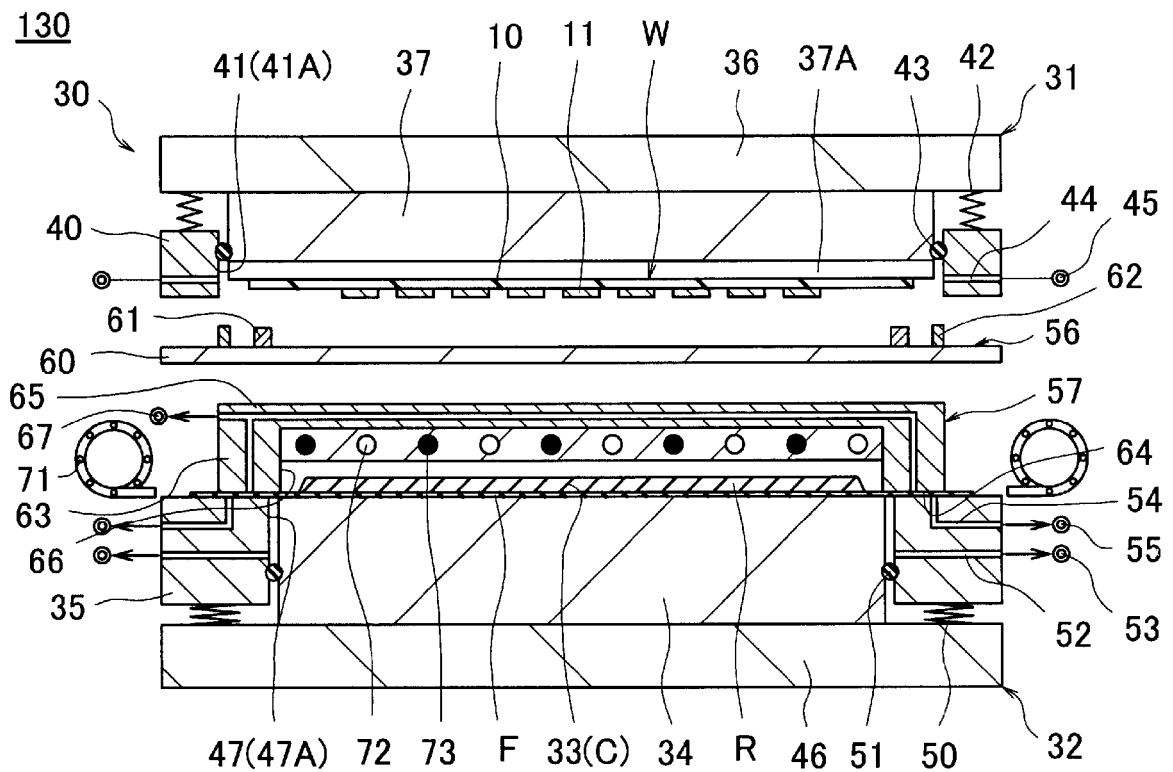
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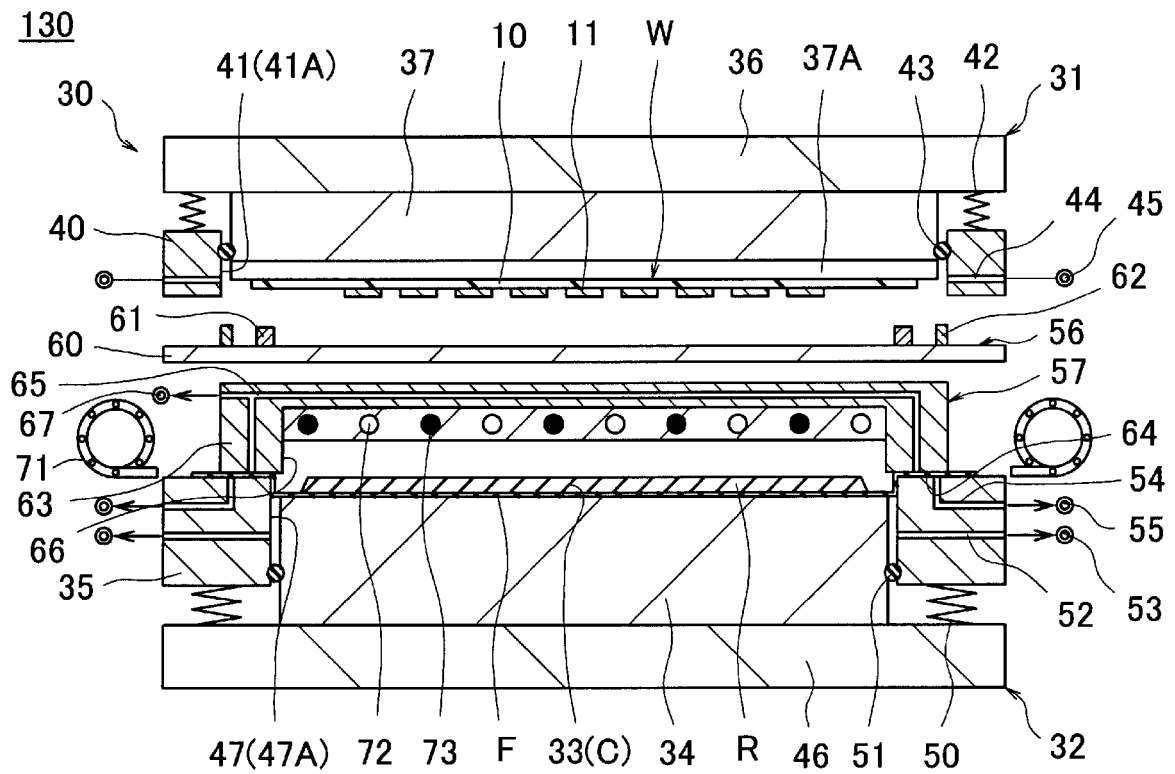
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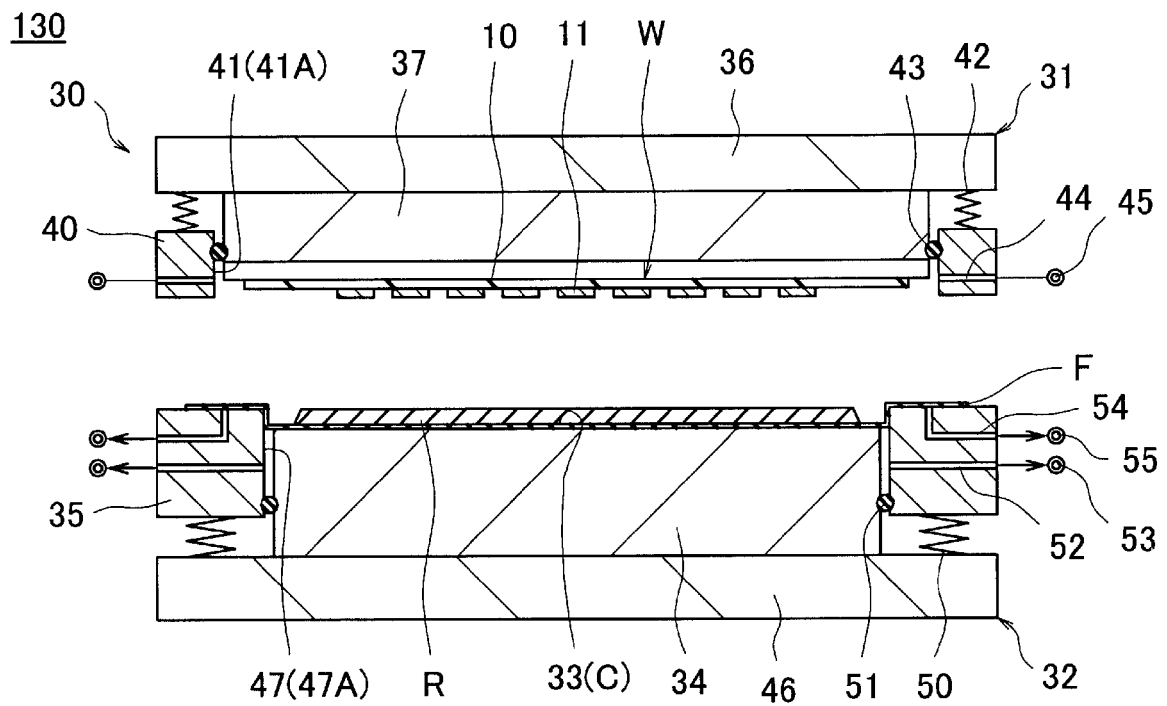
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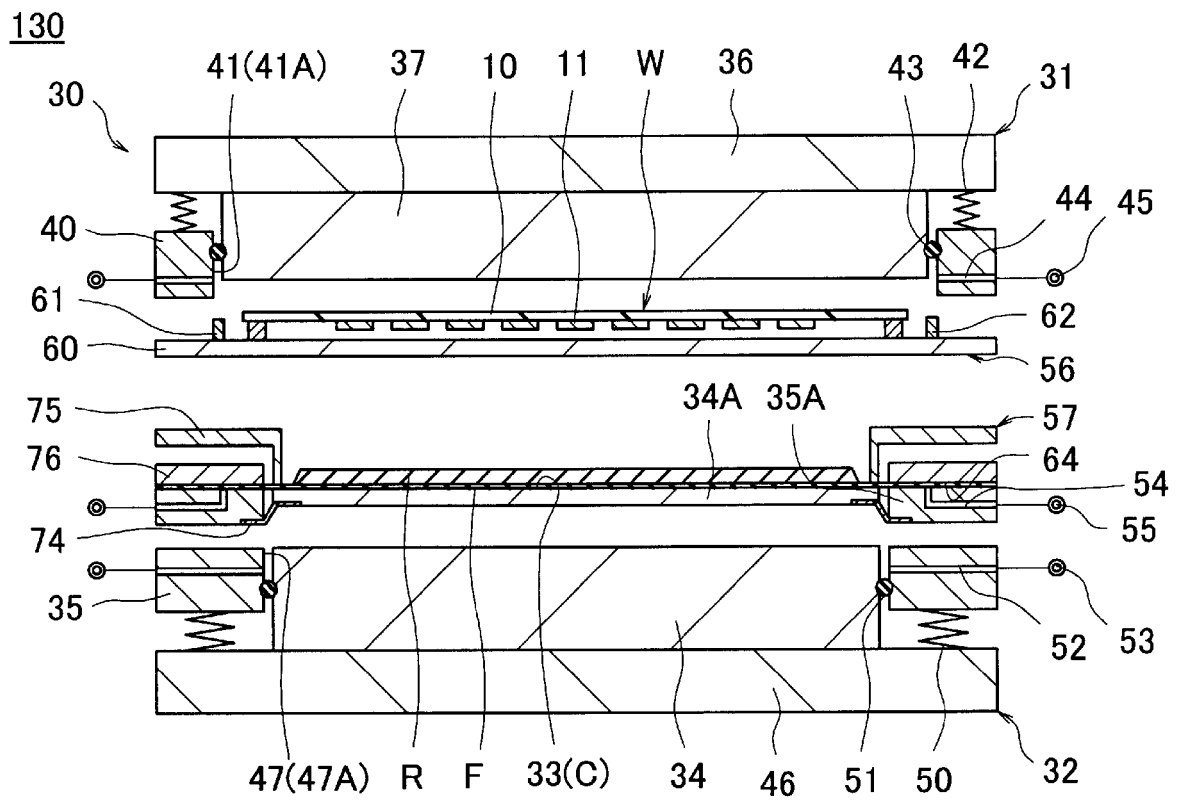
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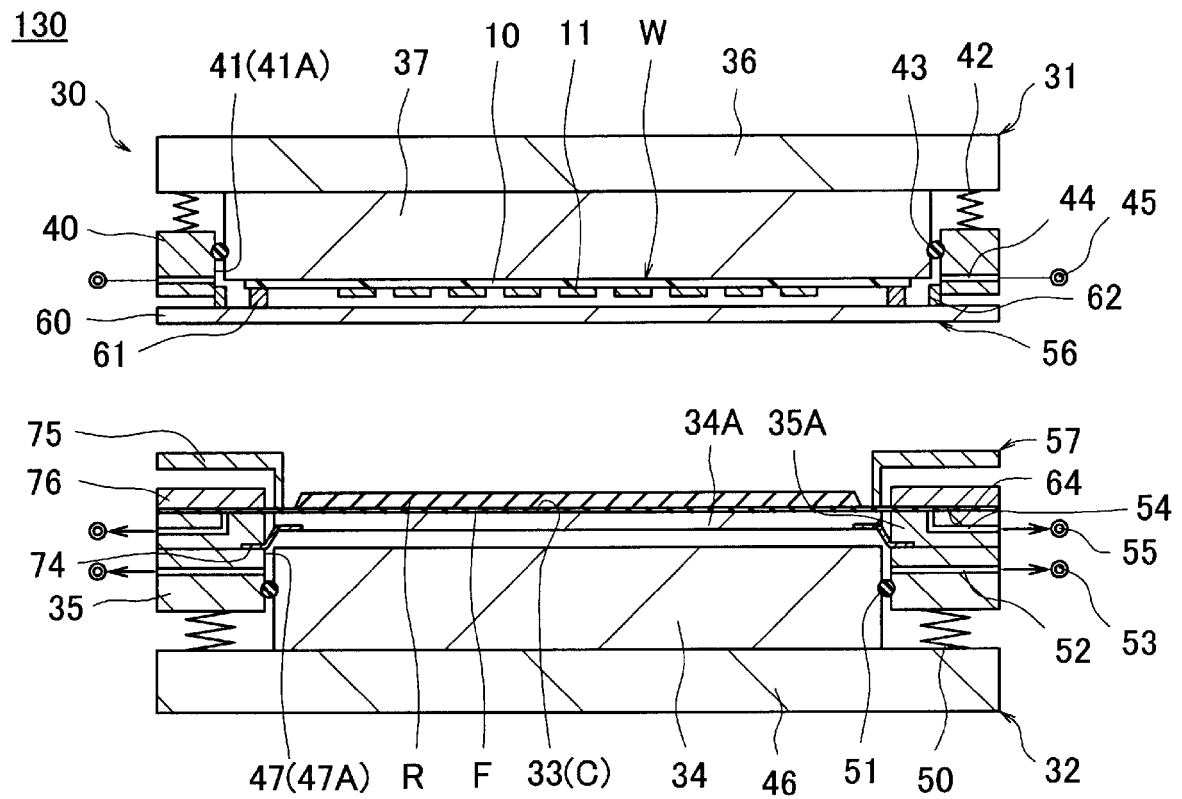
[図14]



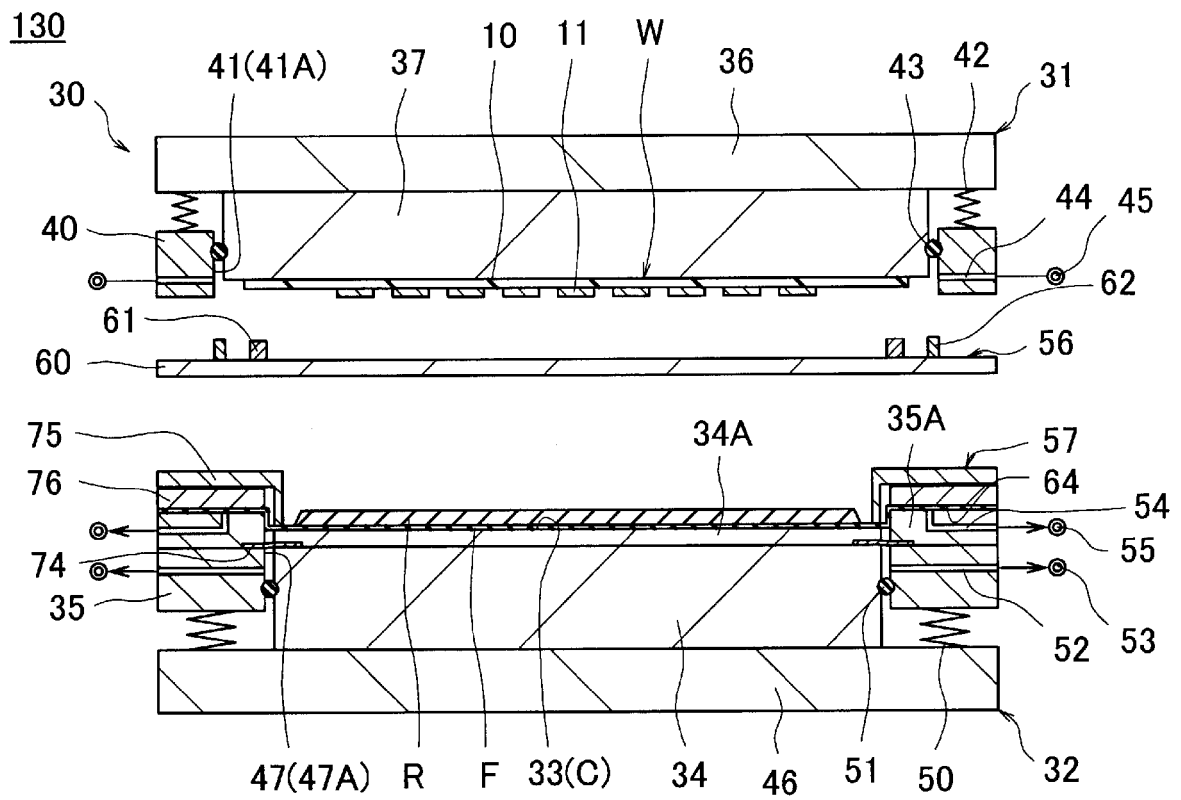
[図15]



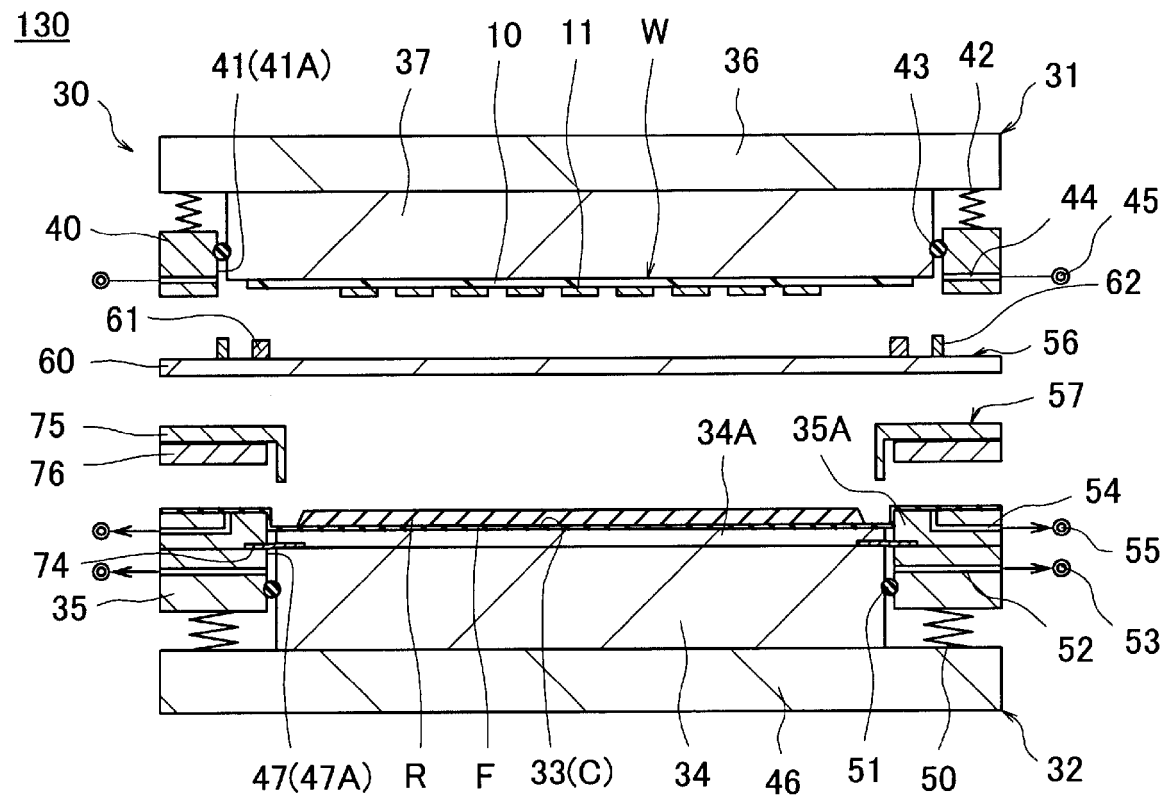
[図16]



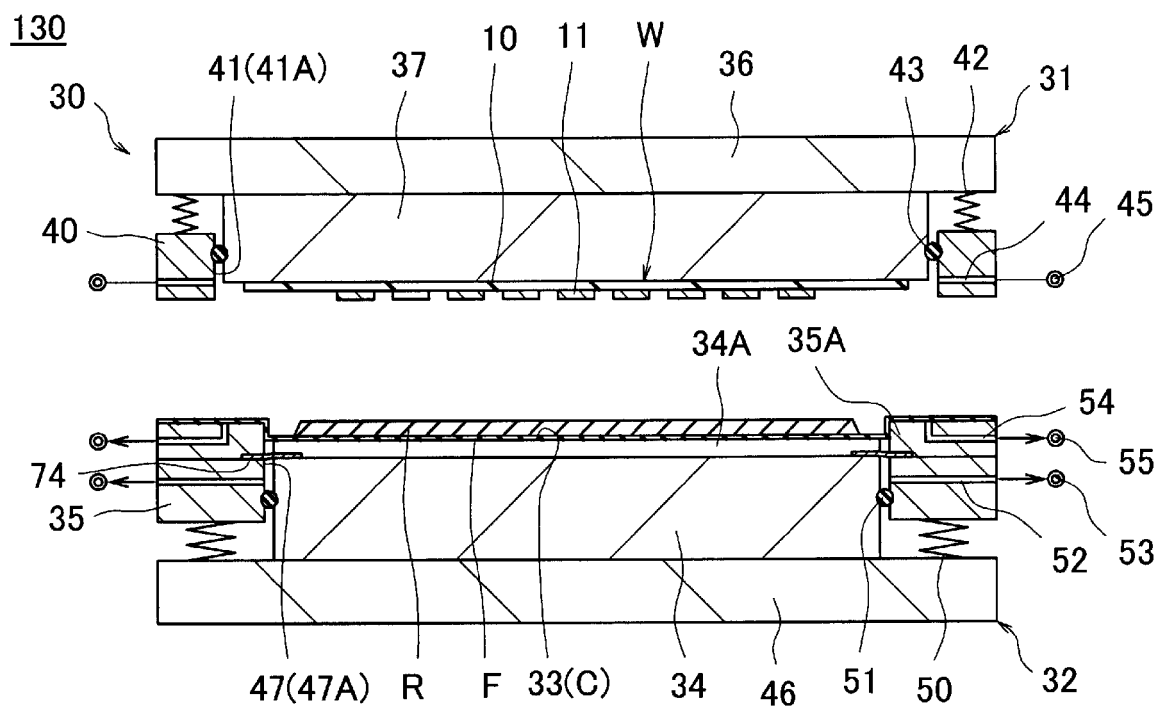
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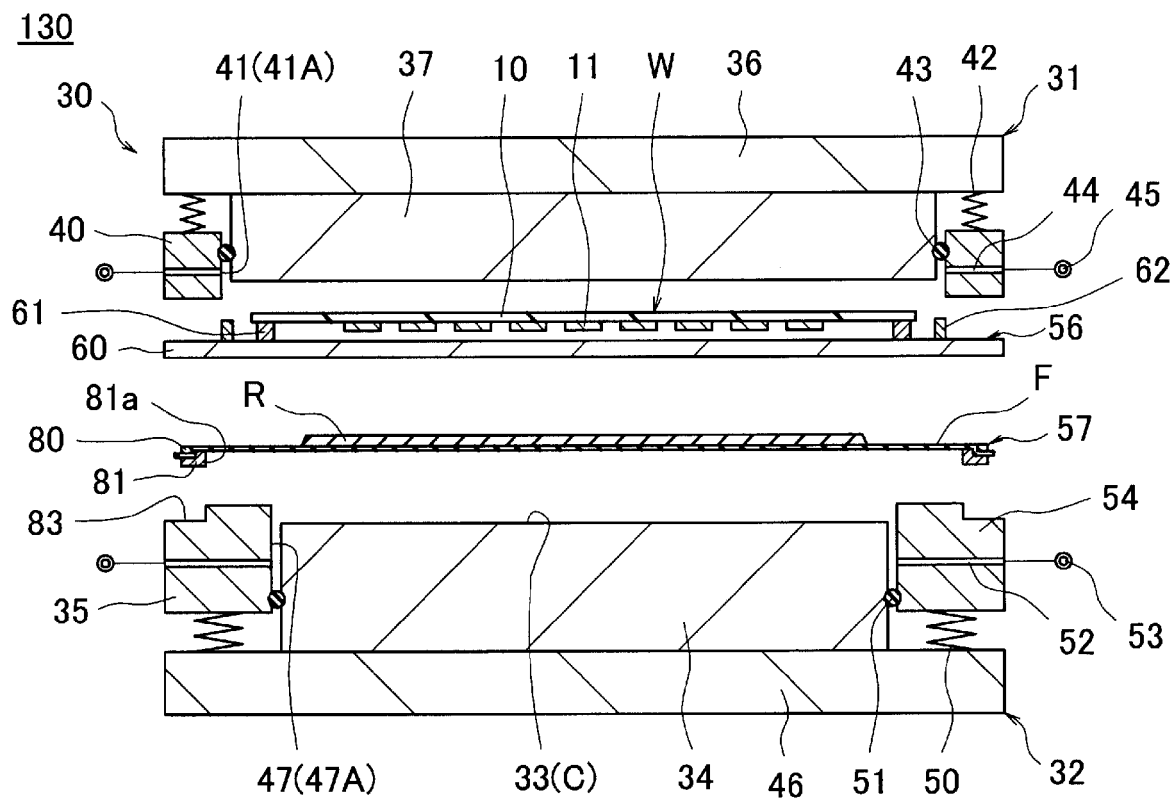
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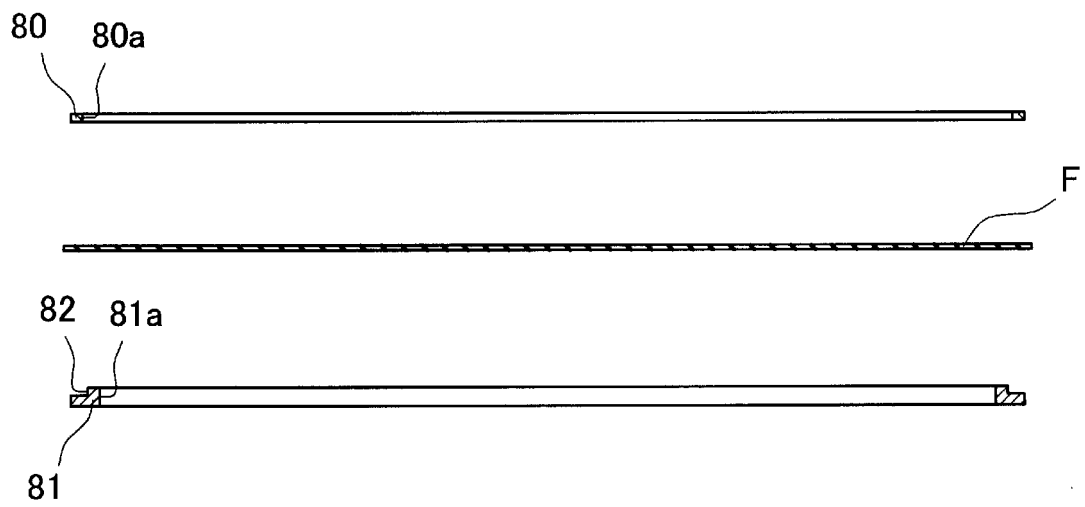
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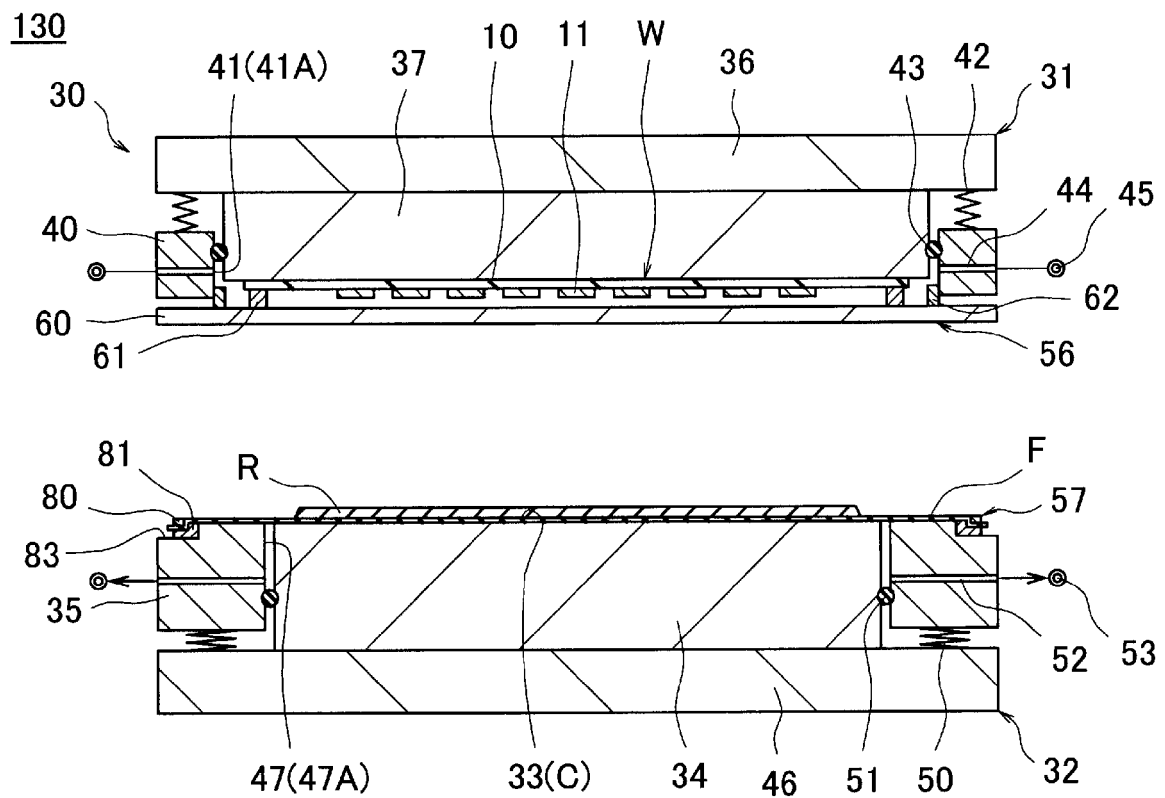
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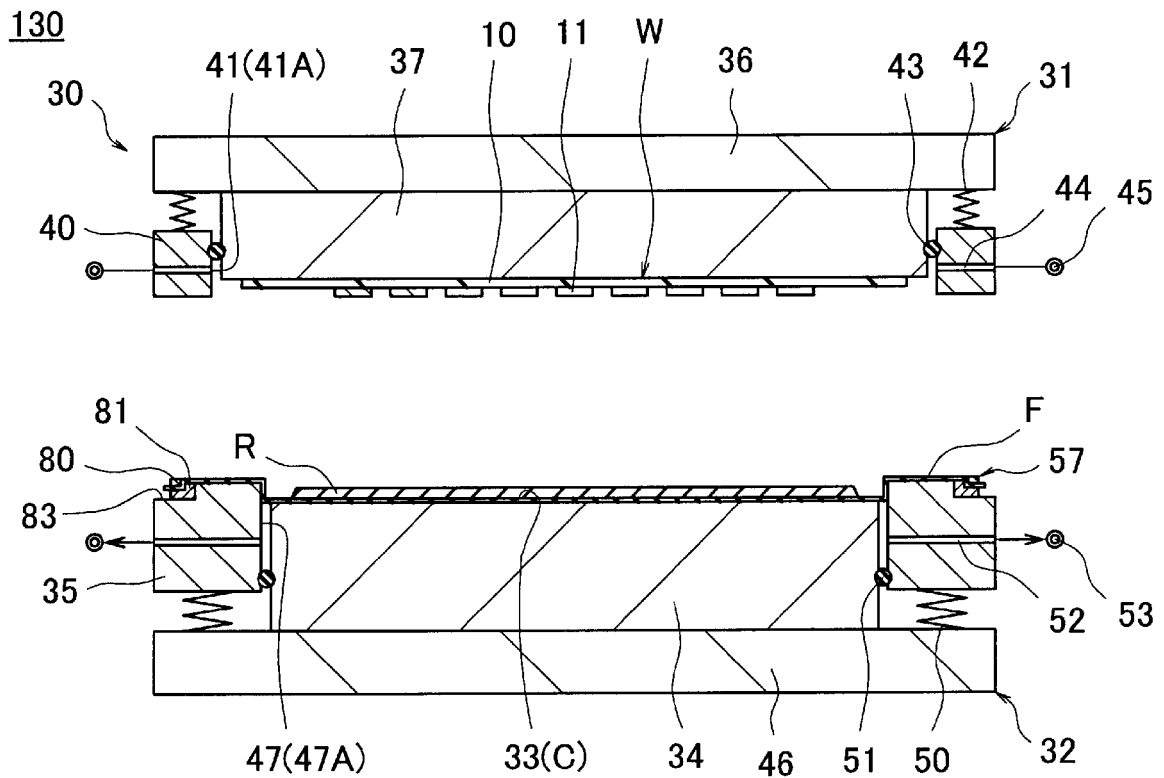
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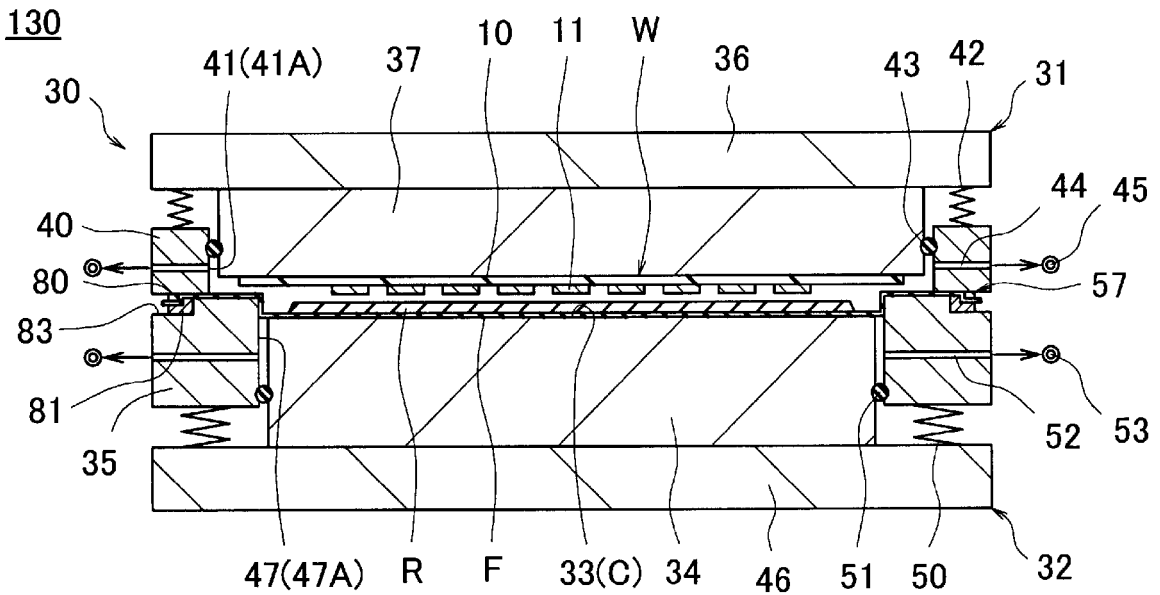
[図22]



[図23]

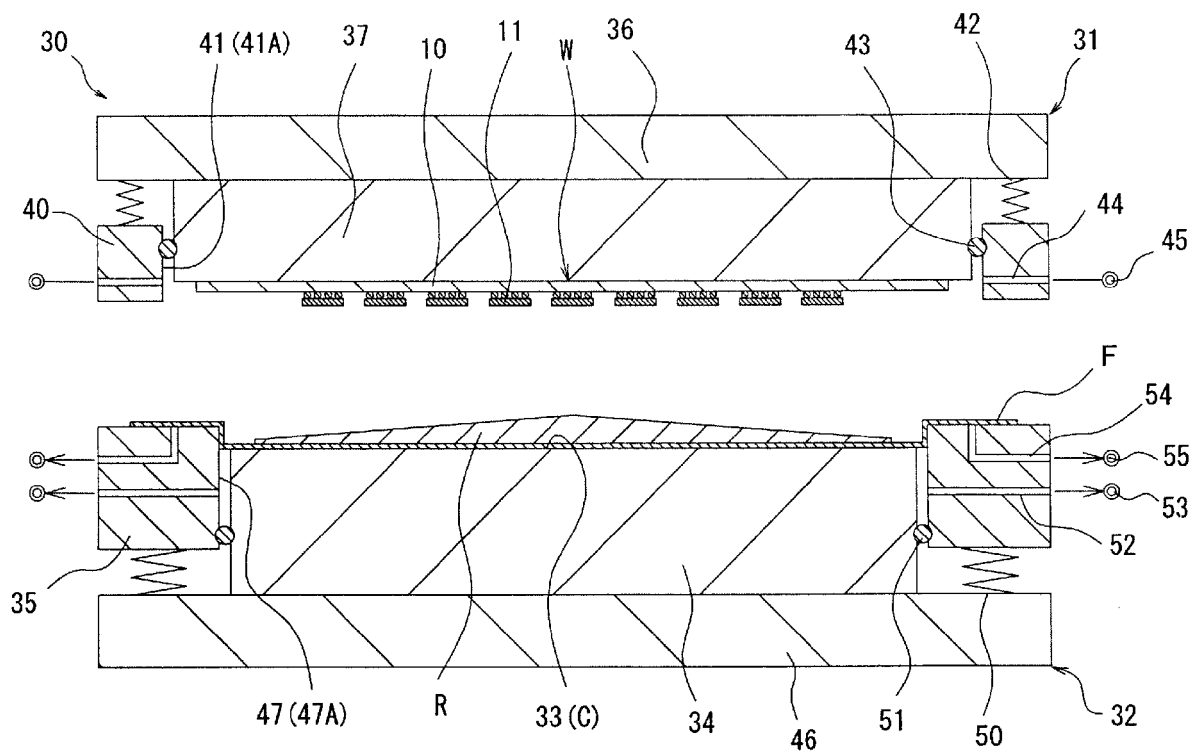


[図24]



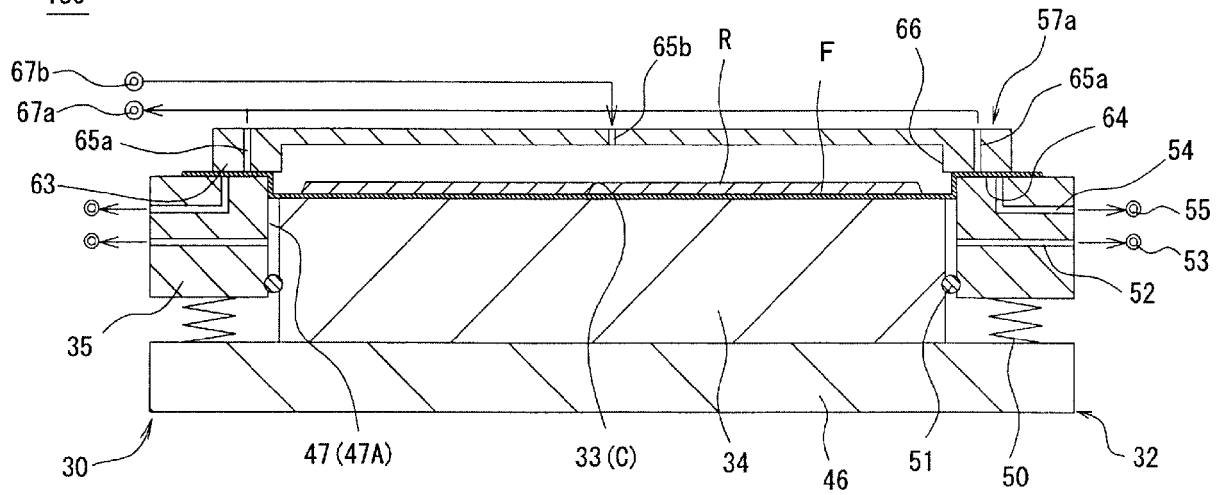


130

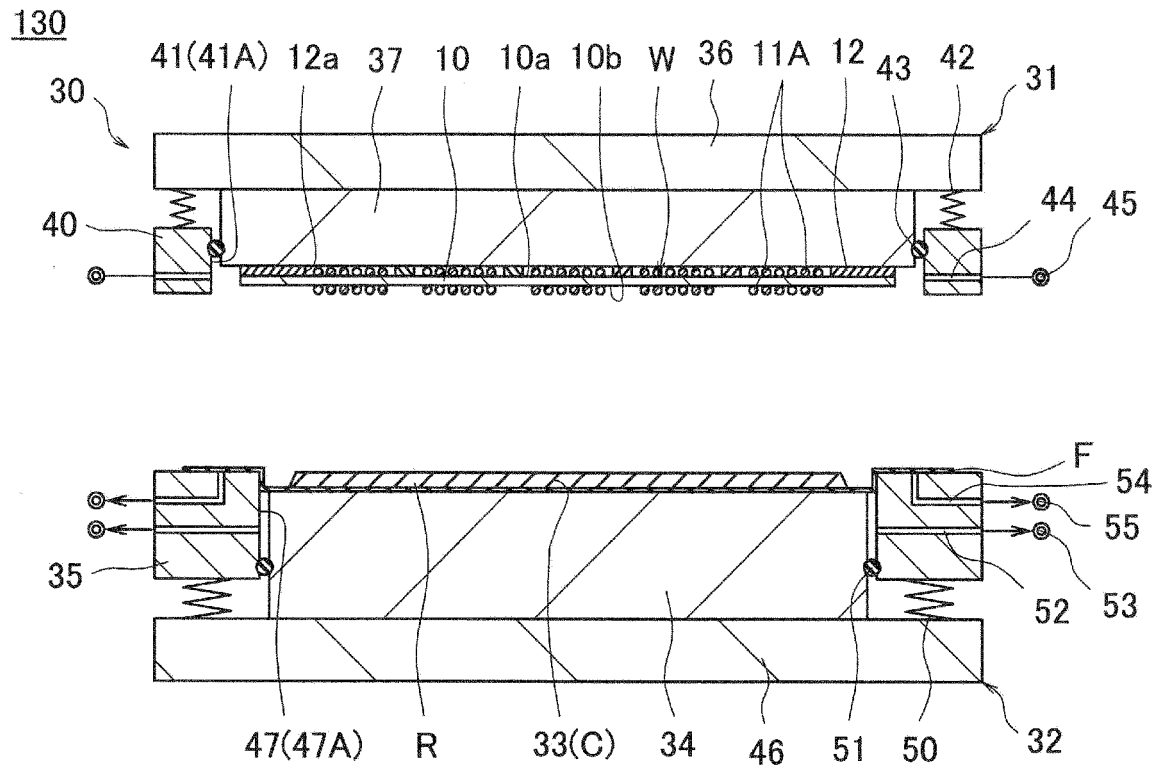


The figure illustrates a semiconductor device 100. The top view shows a rectangular substrate 30 with a central region 33(C) and side regions 32 and 34. Various layers and structures are labeled with reference numerals. The cross-sectional view shows the vertical stack of layers, including a base layer 63, a middle layer 64, and a top layer 65a/b. A force F is applied to the top surface.

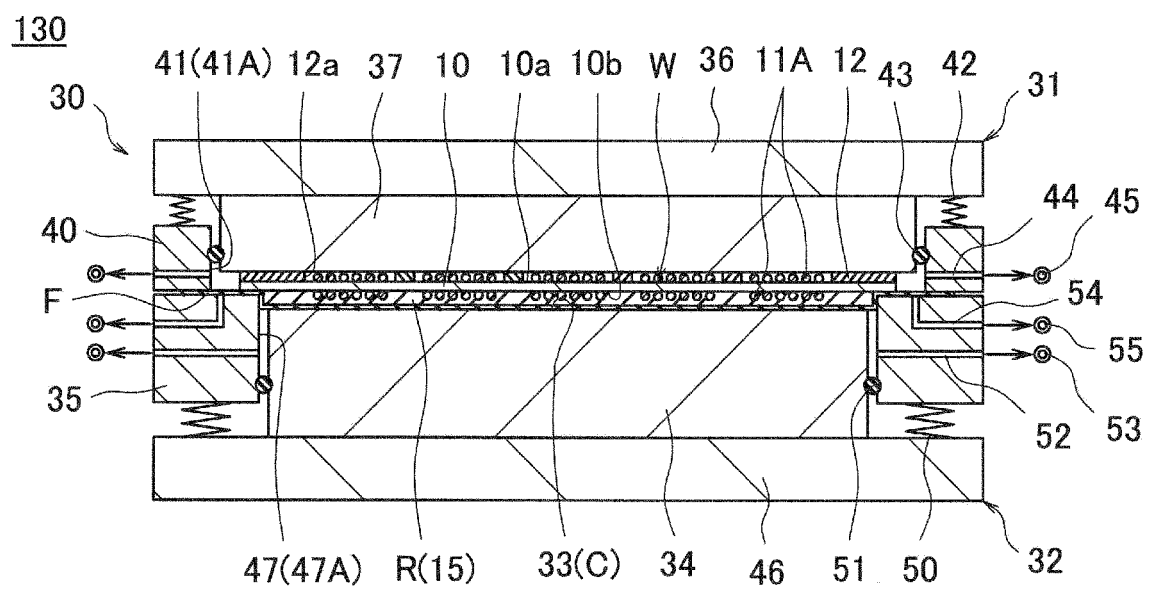
130



[図33]

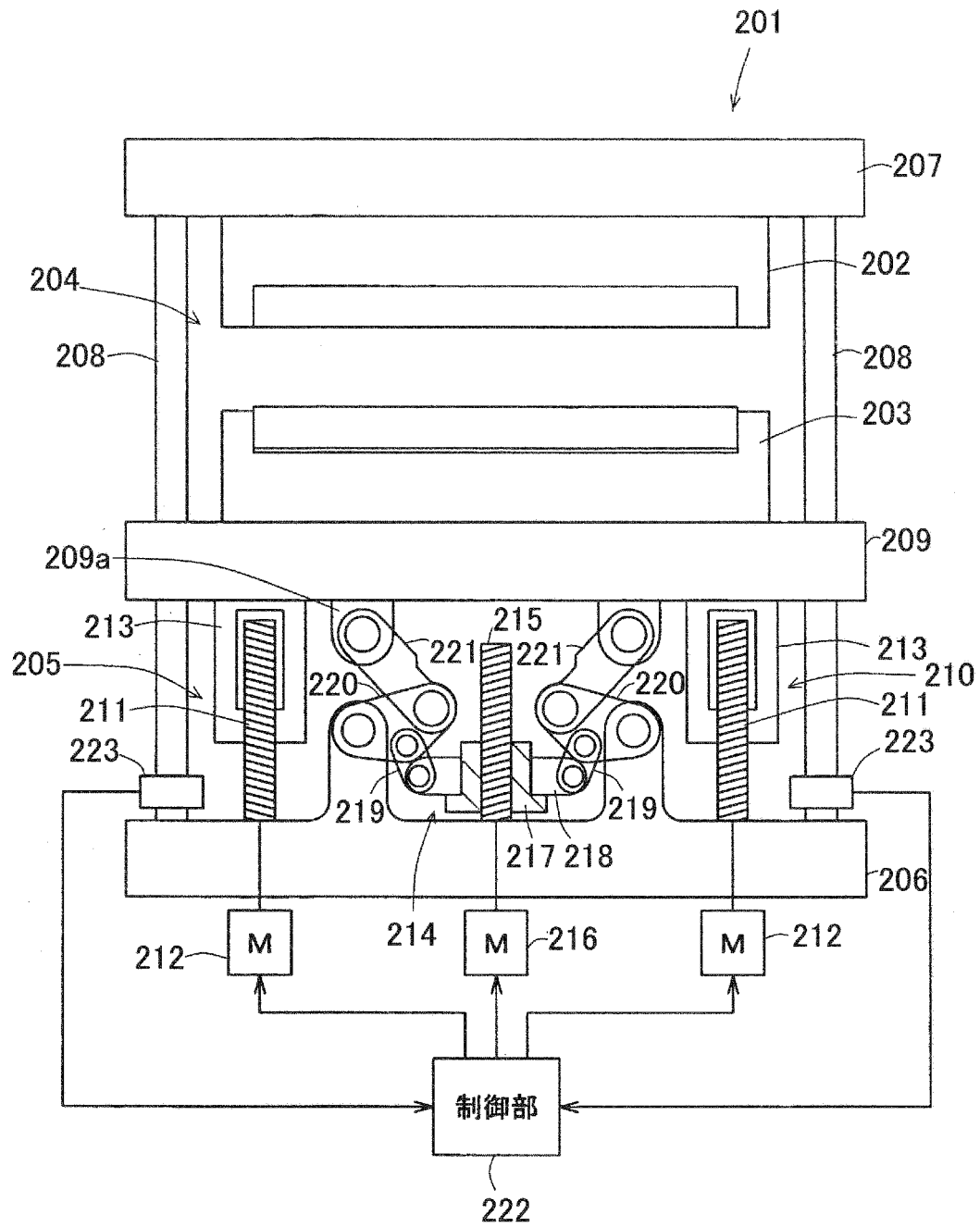


[図34]

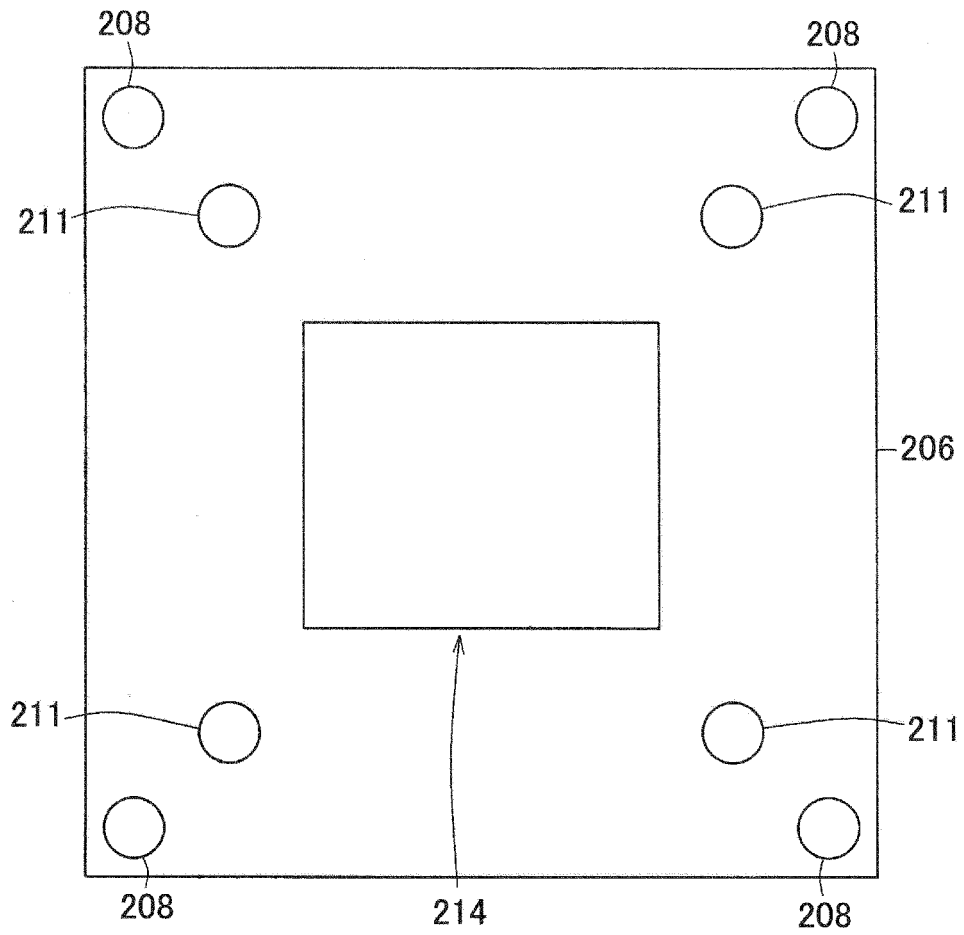




[図37]



[図38]



[図39]

図39A

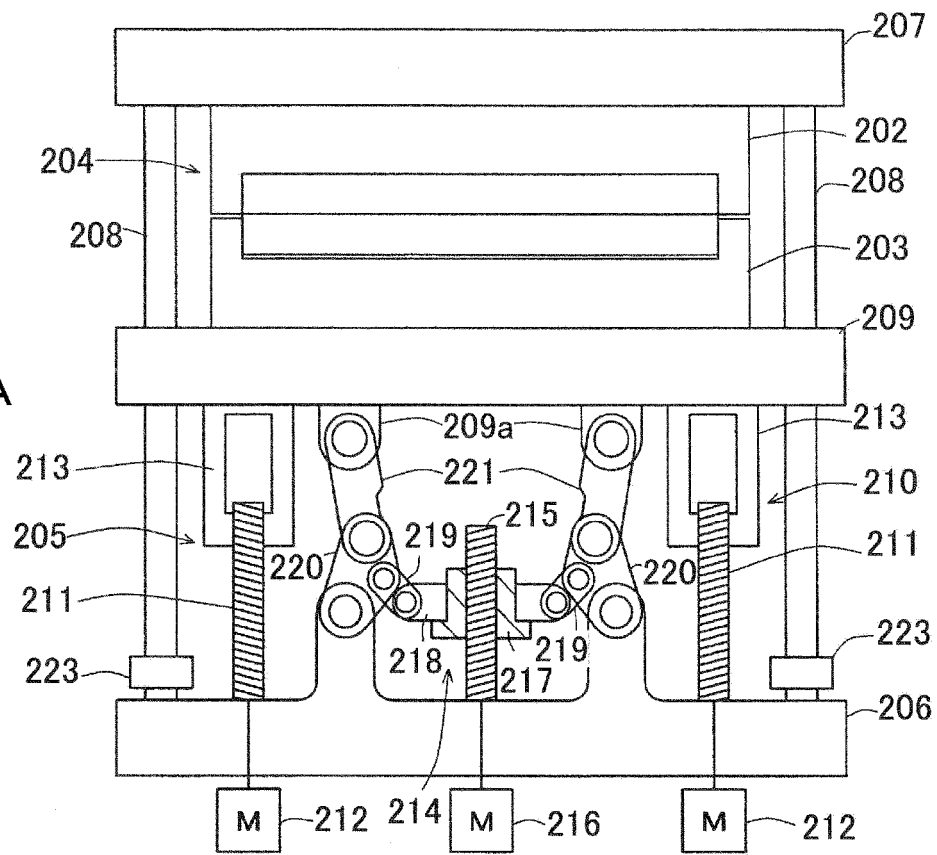
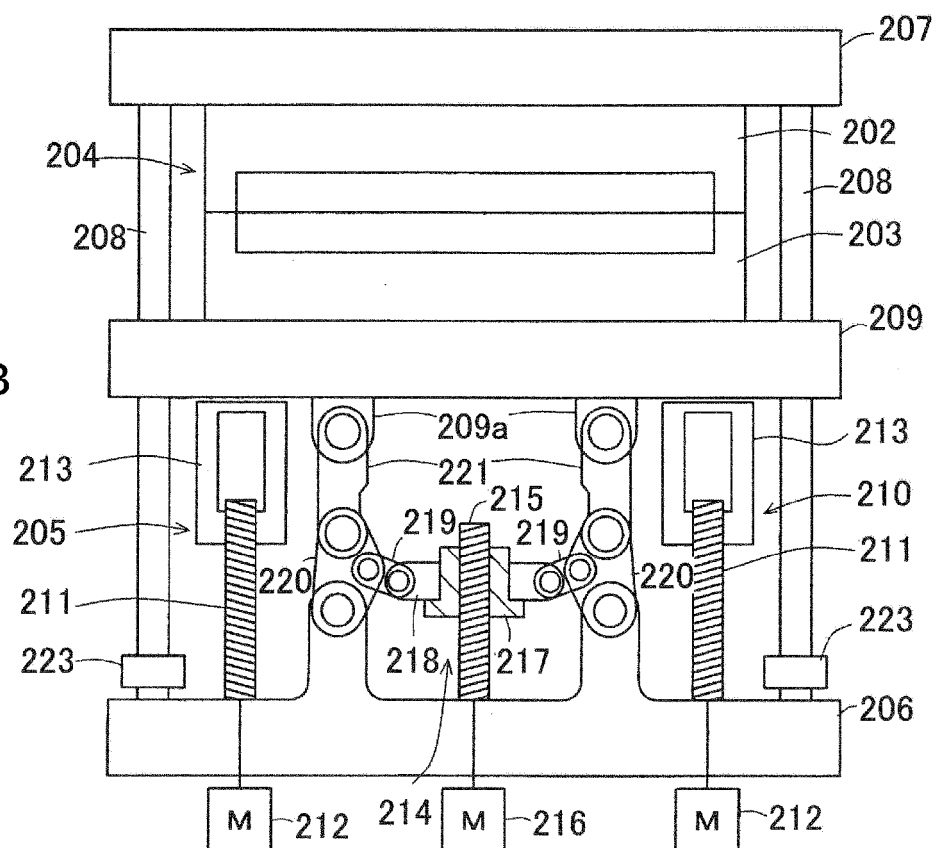


図39B



[図40]

図40A

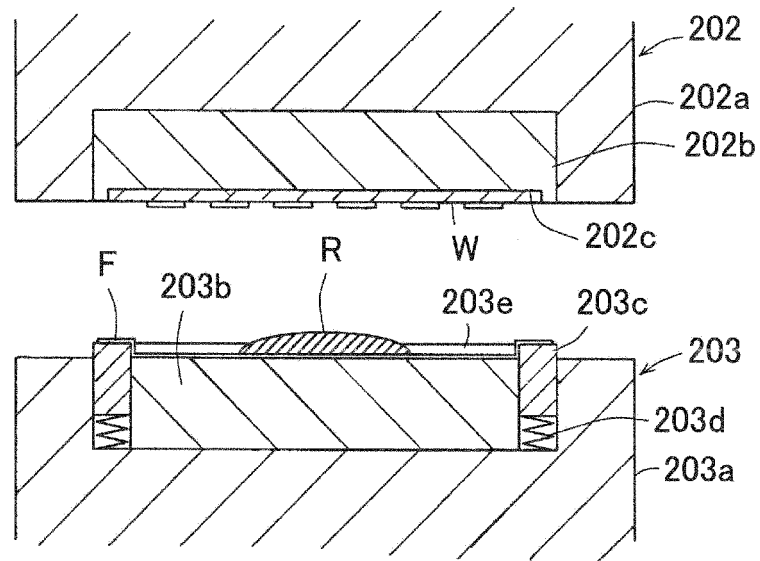


図40B

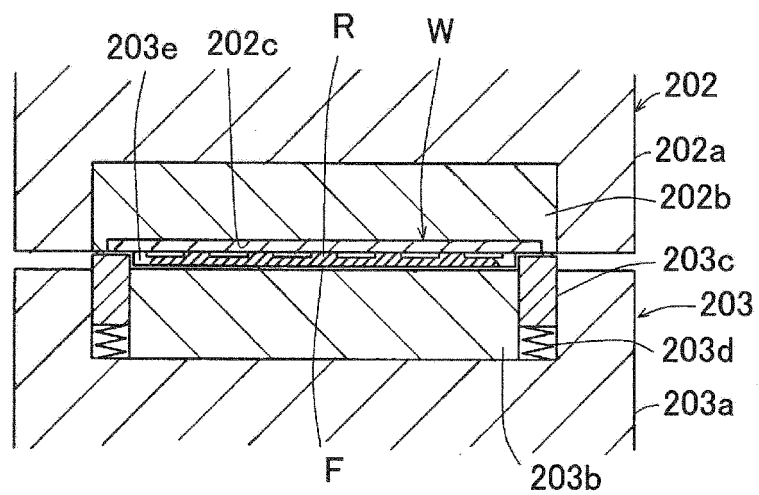


図40C

